

MAGNETORESISTIVE SENSOR MEMORY WITH MULTIFERROIC MATERIAL

ABSTRACT OF THE DISCLOSURE

5 A memory cell includes a magnetoresistive sensor that comprises layers that include a free layer. The magnetoresistive sensor conducts a read current representative of data stored in the memory cell during a read interval. A first write conductor carries a write current that writes data in the free layer. At least one of the layers comprises a multiferroic layer formed of multiferroic material.

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FIGURE 6C